

## Standard Rectifier

$$V_{RRM} = 1200 \text{ V}$$

$$I_{FAV} = 30 \text{ A}$$

$$V_F = 1.25 \text{ V}$$

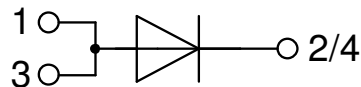
### Single Diode

#### Part number

**DSI30-12AS**



Backside: cathode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

#### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

#### Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

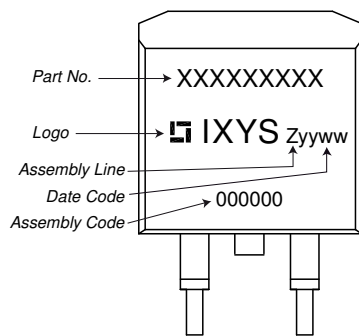
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		40	$\mu\text{A}$
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
$V_F$	forward voltage drop	$I_F = 30$ A		$T_{VJ} = 25^\circ\text{C}$		1.29	V
		$I_F = 60$ A				1.60	V
		$I_F = 30$ A		$T_{VJ} = 150^\circ\text{C}$		1.25	V
		$I_F = 60$ A				1.66	V
$I_{FAV}$	average forward current	$T_C = 130^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		30	A
$V_{FO}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.82	V
$r_F$	slope resistance					14.1	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.9	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.25		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		160	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		300	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		325	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		255	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		275	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		450	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		440	A <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		325	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		315	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		10	pF

Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			35	A
$T_{VJ}$	virtual junction temperature		-40		175	°C
$T_{op}$	operation temperature		-40		150	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				2		g
$F_C$	mounting force with clip		20		60	N

<sup>1)</sup>  $I_{RMS}$  is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

### Product Marking



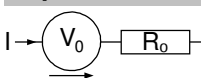
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSI30-12AS	DSI30-12AS	Tape & Reel	800	507511
Alternative	DSI30-12AS-TUB	DSI30-12AS	Tube	50	470988

Similar Part	Package	Voltage class
DSI30-12A	TO-220AC (2)	1200
DSI30-12AC	ISOPLUS220AC (2)	1200
DSI30-16AS	TO-263AB (D2Pak) (2)	1600
DSI30-16A	TO-220AC (2)	1600
DSI30-08AS	TO-263AB (D2Pak) (2)	800
DSI30-08A	TO-220AC (2)	800
DSI30-08AC	ISOPLUS220AC (2)	800

### Equivalent Circuits for Simulation

\* on die level

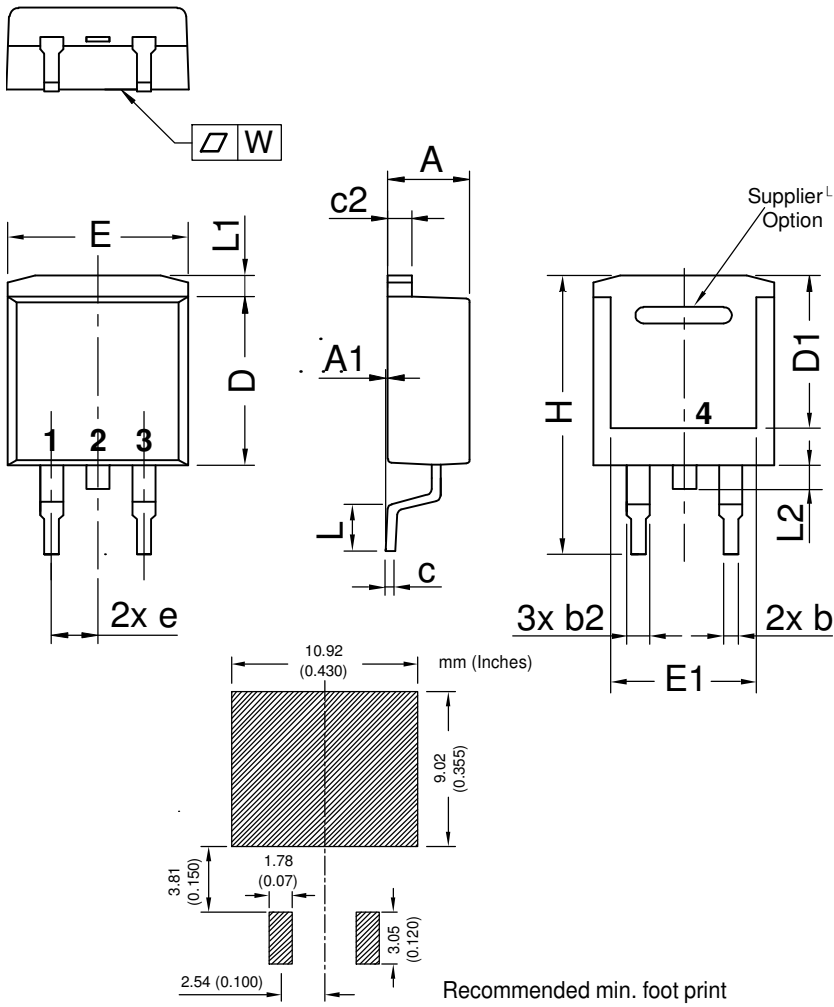
$T_{VJ} = 175\text{ °C}$



**Rectifier**

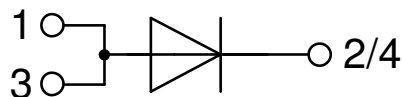
$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	11	mΩ

## Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

*All dimensions conform with and/or within JEDEC standard.*



## Rectifier

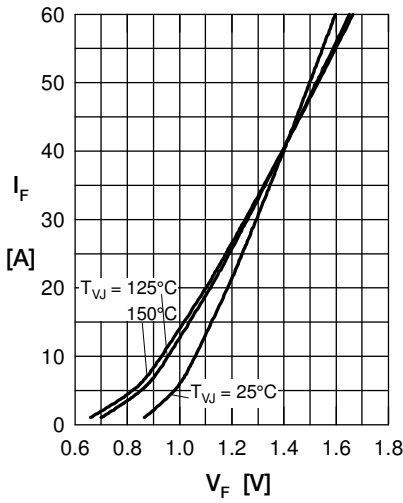


Fig. 1 Forward current versus voltage drop per diode

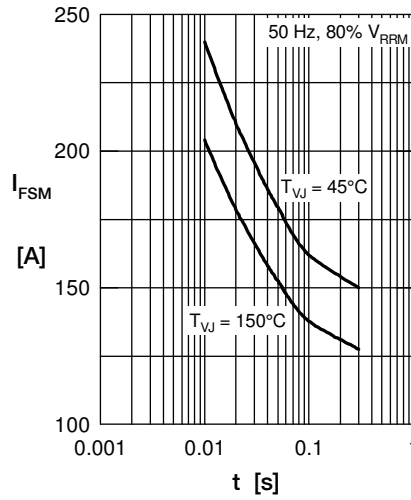


Fig. 2 Surge overload current

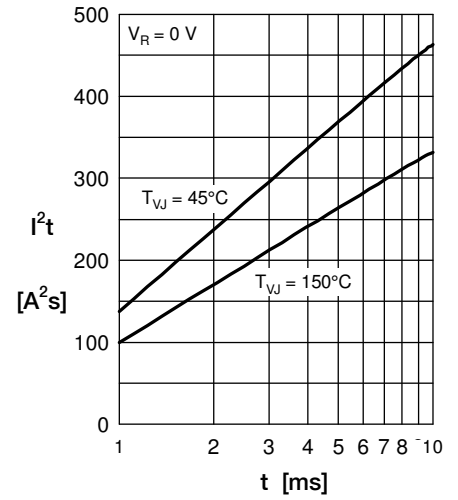


Fig. 3  $I^2t$  versus time per diode

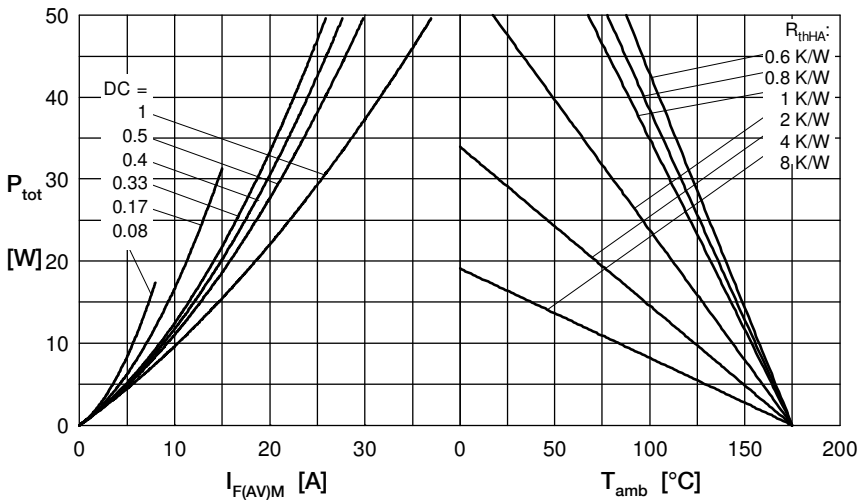


Fig. 4 Power dissipation vs. direct output current and ambient temperature

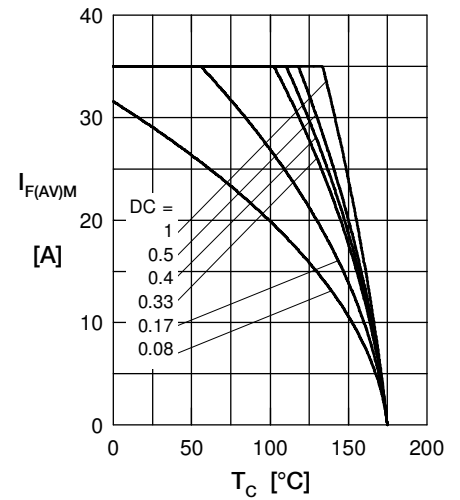


Fig. 5 Max. forward current vs. case temperature

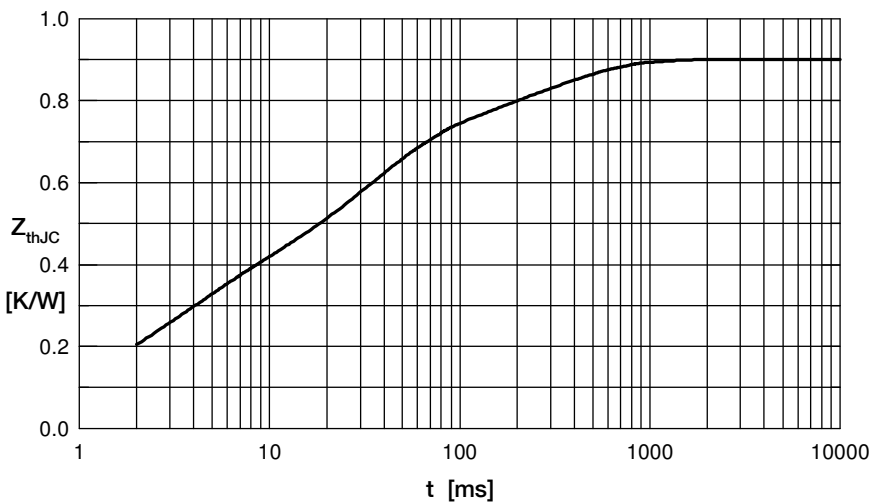


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.03	0.0004
2	0.08	0.002
3	0.2	0.003
4	0.39	0.03
5	0.2	0.29